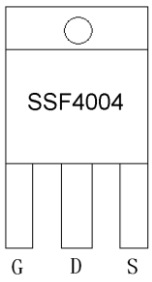
Main Product Characteristics

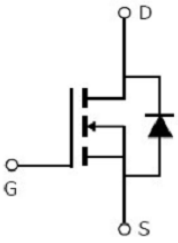
V_{DSS}	40V
R_{DS}(on)	2.3mΩ (typ.)
I_D	180A ①



TO-220



Marking and Pin Assignment



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 175℃ operating temperature

Description

SSF4004S utilizes the latest processing techniques to achieve high cell density and reduces on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute Max Rating

Symbol	Parameter	Max.	Units
I_D @ TC = 25°C	Continuous Drain Current, V_{GS} @ 10V(Silicon Limited)	180 ①	A
I_D @ TC = 100°C	Continuous Drain Current, V_{GS} @ 10V	120 ①	
I_D @ TC = 25°C	Continuous Drain Current, V_{GS} @ 10V(Package Limited)	75	
I_{DM}	Pulsed Drain Current ②	710	
P_D @TC = 25°C	Power Dissipation ③	200	W
	Linear Derating Factor	1.3	W/°C
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy @ L=0.3mH	960	mJ
I_{AS}	Avalanche Current @ L=0.3mH	80	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C

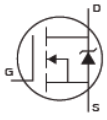
Thermal Resistance

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ③	—	0.75	℃/W
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s) ④	—	62	℃/W

Electrical Characteristics @T_A=25℃ unless otherwise specified

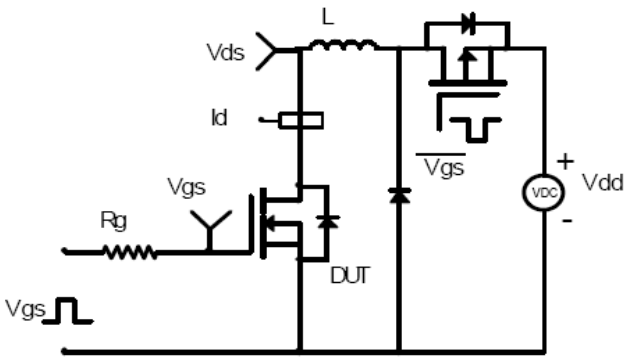
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	40	—	—	V	V_{GS} = 0V, I_D = 250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	2.3	4	mΩ	V_{GS}=10V,I_D = 75A
		—	4.1	—		T_J = 125°C
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	V_{DS} = V_{GS}, I_D = 250μA
		—	2.1	—		T_J = 125°C
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	V_{DS} = 40V,V_{GS} = 0V
		—	—	50		T_J = 125°C
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V_{GS} = 20V
		—	—	-100		V_{GS} = -20V
Q_g	Total gate charge	—	278	—	nC	I_D = 75A,
Q_{gs}	Gate-to-Source charge	—	41	—		V_{DS}=32V,
Q_{gd}	Gate-to-Drain("Miller") charge	—	119	—		V_{GS} = 10V
$t_{d(on)}$	Turn-on delay time	—	71	—	ns	V_{GS}=10V, V_{DS} =20V, R_{GEN}=3Ω,I_D =1.3A
t_r	Rise time	—	34	—		
$t_{d(off)}$	Turn-Off delay time	—	131	—		
t_f	Fall time	—	106	—		
C_{iss}	Input capacitance	—	12968	—	pF	V_{GS} = 0V
C_{oss}	Output capacitance	—	940	—		V_{DS} = 40V
C_{rss}	Reverse transfer capacitance	—	905	—		f = 1MHz

Source-Drain Ratings and Characteristics

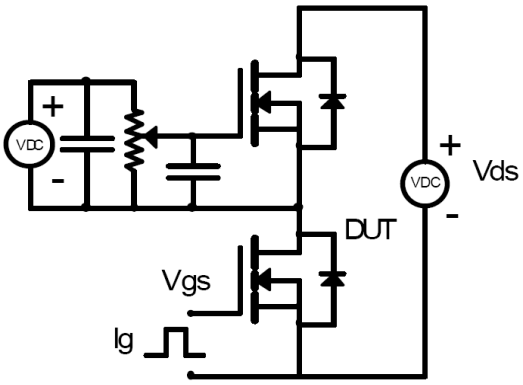
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	75 ①	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	750	A	
V_{sd}	Diode Forward Voltage	—	—	1.3	V	I_S=30A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	—	28	—	nS	T_J = 25°C, I_F =70A, di/dt = 100A/μs
Q_{rr}	Reverse Recovery Charge	—	20	—	nC	

Test circuits and Waveforms

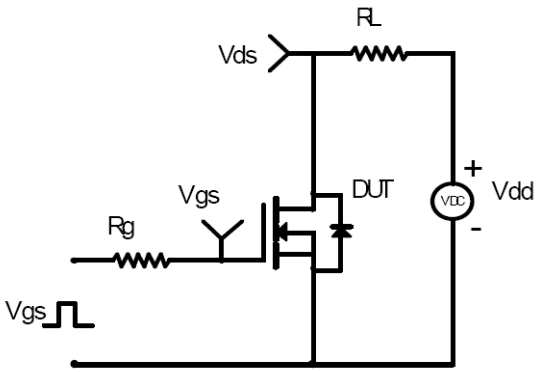
EAS Test Circuit



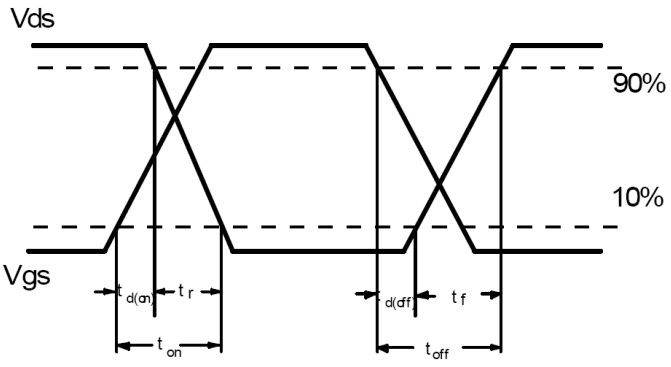
Gate charge test circuit



Switching Time Test Circuit



Switching Waveforms



Notes:

①Calculated continuous current based on maximum allowable junction temperature.

②Repetitive rating; pulse width limited by max. junction temperature.

③The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

④The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25°C

Typical electrical and thermal characteristics

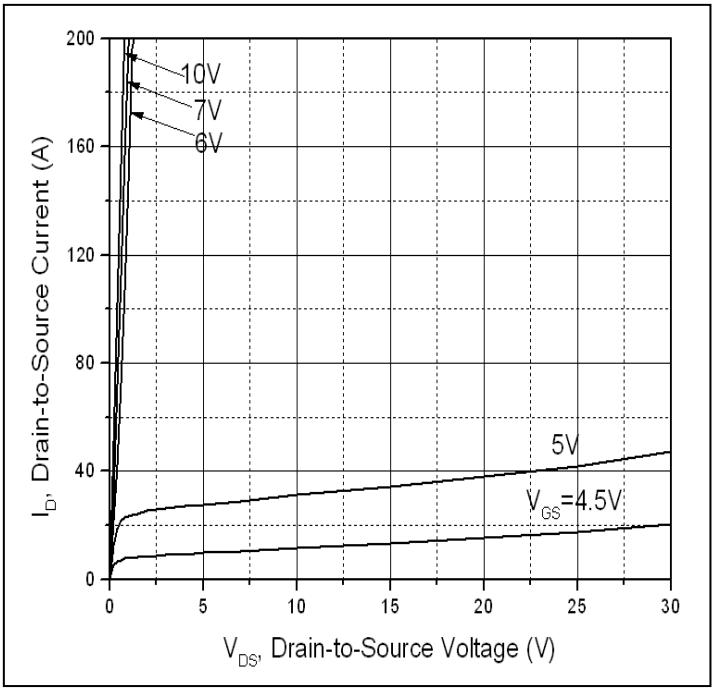


Figure 1.Typical Output Characteristics

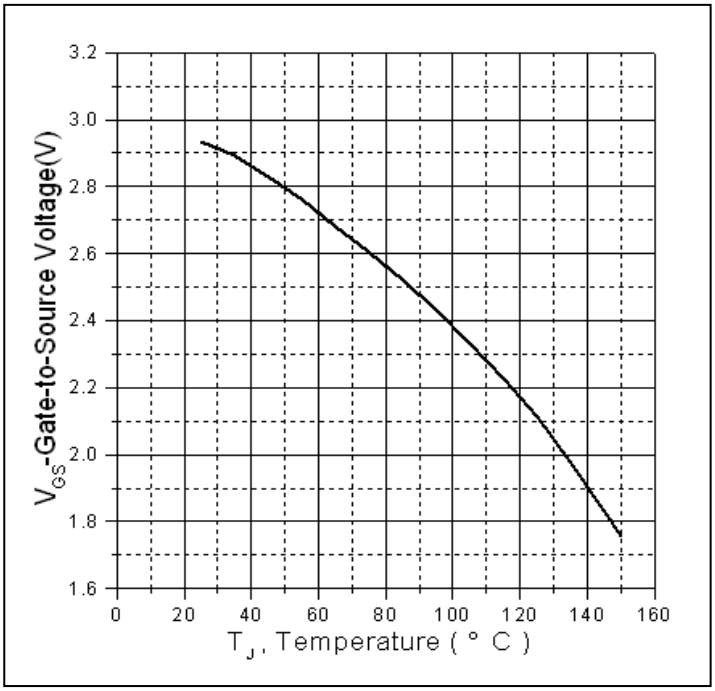


Figure 2. Gate to source cut-off voltage

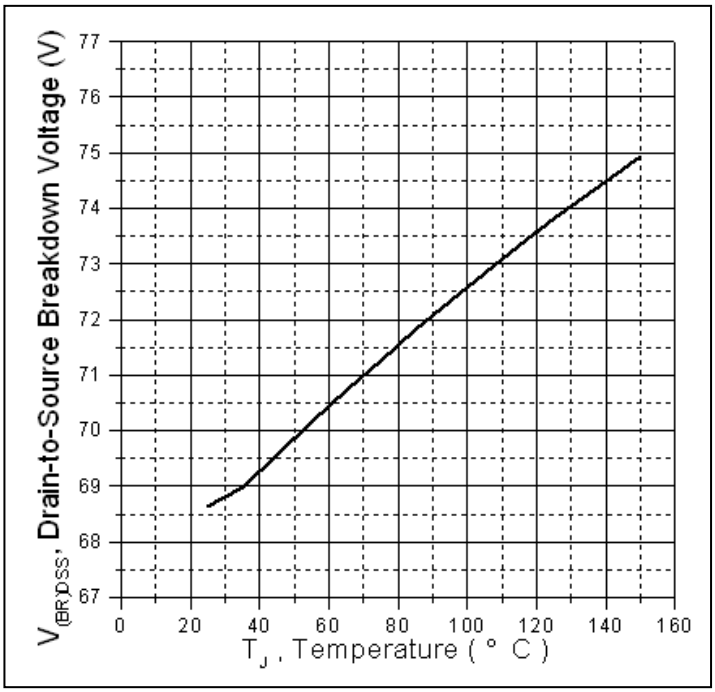


Figure 3. Drain-to-Source Breakdown Voltage Vs. Case Temperature

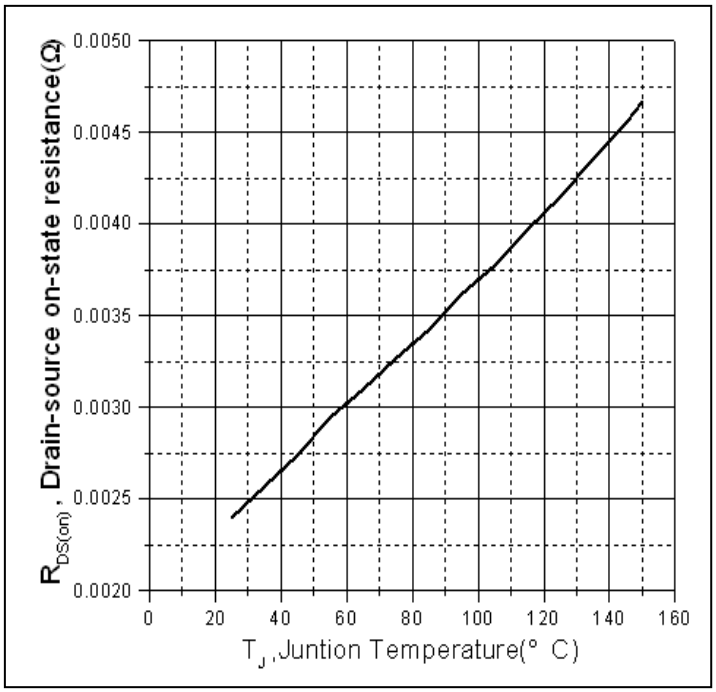


Figure 4.Normalized On-Resistance Vs. Case Temperature

Typical electrical and thermal characteristics

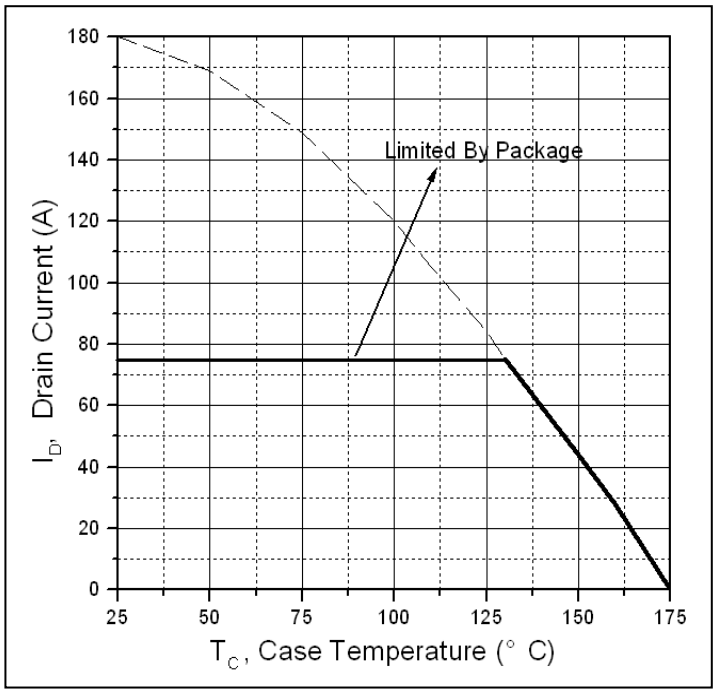


Figure 5. Maximum Drain Current Vs. Case Temperature

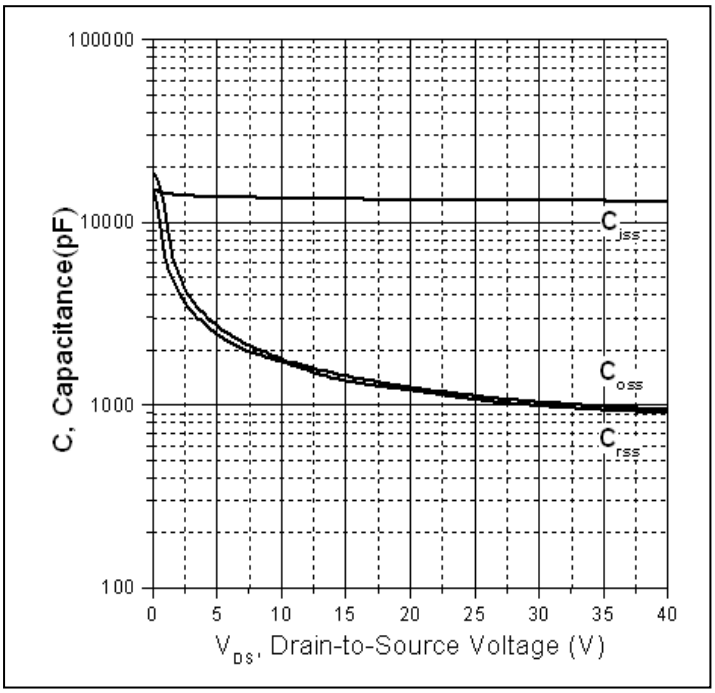


Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

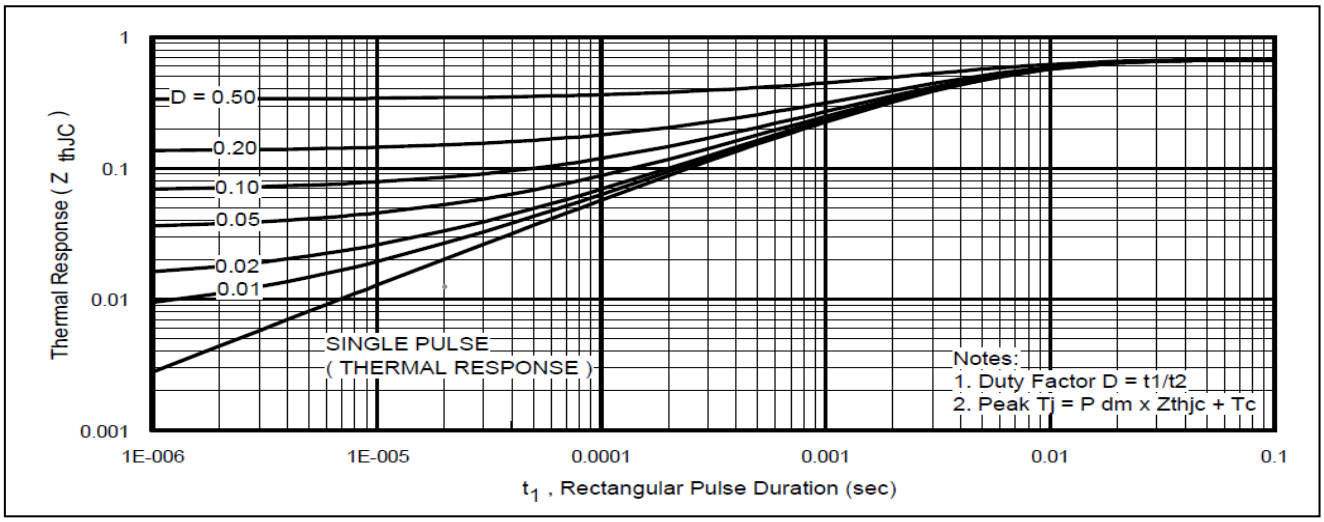
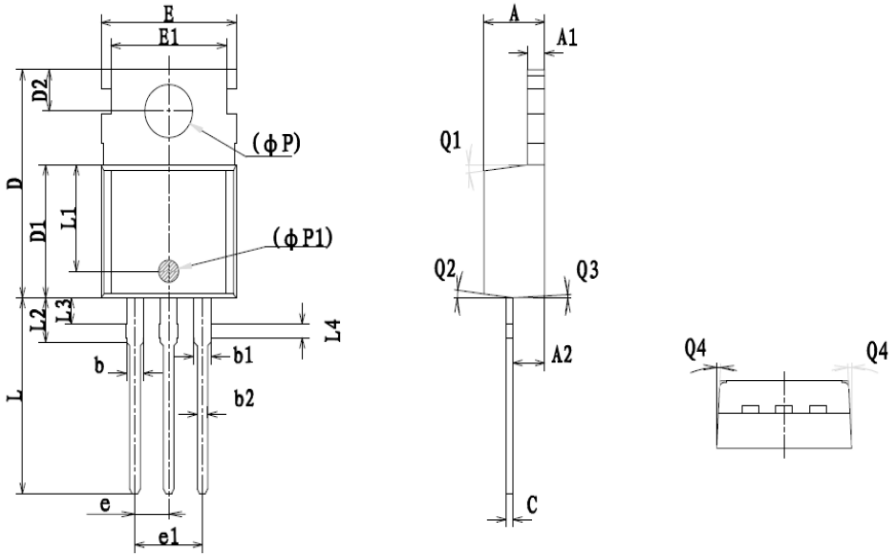


Figure7. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Mechanical Data：

TO220 PACKAGE OUTLINE DIMENSION_GN



Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	4.400	4.550	4.700	0.173	0.179	0.185
A1	1.270	1.300	1.330	0.050	0.051	0.052
A2	2.240	2.340	2.440	0.088	0.092	0.096
b	–	1.270	–	-	0.050	-
b1	1.270	1.370	1.470	0.050	0.054	0.058
b2	0.750	0.800	0.850	0.030	0.031	0.033
C	0.480	0.500	0.520	0.019	0.020	0.021
D	15.100	15.400	15.700	0.594	0.606	0.618
D1	8.800	8.900	9.000	0.346	0.350	0.354
D2	2.730	2.800	2.870	0.107	0.110	0.113
E	9.900	10.000	10.100	0.390	0.394	0.398
E1	-	8.700	-	-	0.343	-
ΦP	3.570	3.600	3.630	0.141	0.142	0.143
ΦP1	1.400	1.500	1.600	0.055	0.059	0.063
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
L	13.150	13.360	13.570	0.518	0.526	0.534
L1	7.35REF			0.29REF		
L2	2.900	3.000	3.100	0.114	0.118	0.122
L3	1.650	1.750	1.850	0.065	0.069	0.073
L4	0.900	1.000	1.100	0.035	0.039	0.043
Q1	5^0	7^0	9^0	5^0	7^0	9^0
Q2	5^0	7^0	9^0	5^0	7^0	9^0
Q3	5^0	7^0	9^0	5^0	7^0	9^0
Q4	1^0	3^0	5^0	1^0	3^0	5^0

Ordering and Marking Information

Device Marking: SSF4004

Package (Available)

TO-220

Operating Temperature Range

C : -55 to 175 ºC

Devices per Unit

Package Type	Units/ Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO-220	50	20	1000	6	6000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T_j=150℃ @ 80% of Max V_{DSS}/V_{CES}/VR	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T_j=150℃ @ 100% of Max V_{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices

ATTENTION:

- Any and all Silikron products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Silikron representative nearest you before using any Silikron products described or contained herein in such applications.
- Silikron assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Silikron products described or contained herein.
- Specifications of any and all Silikron products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- Silikron Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all Silikron products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Silikron Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. Silikron believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Silikron product that you intend to use.

Customer Service

Worldwide Sales and Service:

Sales@silikron.com

Technical Support:

Technical@silikron.com

Suzhou Silikron Semiconductor Corp.

11A, 428 Xinglong Street, Suzhou Industrial Park, P.R.China

TEL: (86-512) 62560688

FAX: (86-512) 65160705

E-mail: Sales@silikron.com